

ZN501AJ/ZN502E/CJ

T-51-10-10

10-BIT MICROPROCESSOR COMPATIBLE A-D CONVERTERS

The ZN501 and ZN502 range of successive approximation A-D converters combine several innovations to provide this function on a fully monolithic silicon integrated circuit. The runction on a fully monolitric silicon integrated circuit. The chip consists of a current switching array (requiring no trim), successive approximation logic, 2.5V precision reference, reference amplifier, comparator and three-state output

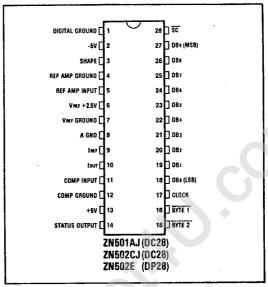
With the aid of BYTE 1 and BYTE 2 the 10 bits of O/P data can be read as a 10-bit word or as 8- and 2-bit words.

FEATURES

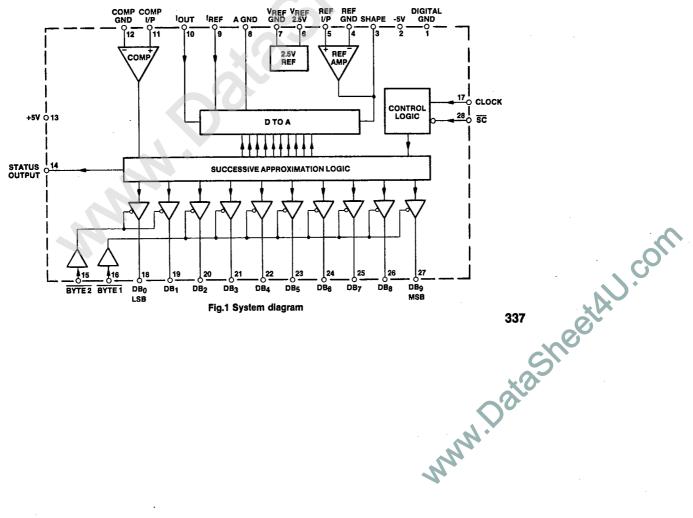
- Choice of Linearity: 1/2 LSB ZN501, 1 LSB ZN502
- Three-State Outputs, TTL Compatible
- 15 microseconds Typical, 20 microseconds Guaranteed Conversion Time
- Input Range as Desired
- Asynchronous START CONVERT
- +5V, -5V Supplies, Microprocessor and TTL/CMOS Compatible
- Commercial or Military Temperature Ranges
- Full 8- or 16-Bit MICRO-Bus Interface
- Available in Ceramic or Moulded Package

ORDERING INFORMATION

Device type	Operating temperature	Package
ZN502E	0°C to +70°C	DP28
ZN502CJ	0°C to +70°C	DC28
ZN501AJ	-55°C to +125°C	DC28



Pin connections - top view



PLESSEY SEMICONDUCTORS **ABSOLUTE MAXIMUM RATINGS**

Supply voltage Vcc+ Supply voltage Vcc-Logic input voltage Operating temperature range

Storage temperature range

T-51-10-10

+7V -7V +Vcc and 0V 0°C to 70°C (ZN502E, ZN502CJ) -55°C to +125°C (ZN501AJ) -55°C to +125°C

ELECTRICAL CHARACTERISTICS (at +5 and -5V supplies and internal reference unless otherwise specified).

		T _{amb} = + 25°C			Over	Spec		
Parameter	Version	Min.	Тур.	Max.	Min.	Max.	Units	Conditions
	ZN501AJ							
Linearity error				±0.5		±0.5	LSB	
Diff. linearity error				±0.75		±0.75		Note 1
Unipolar offset			±0.55	± 1.0		± 1.0		Ext. Ref.
			±0.55	± 1.0		±1.0		Int. Ref.
Bipolar offset			±0.55	± 1.0		±1.0		Ext. Ref.
			±0.55	±1.0		± 1.0		Int. Ref.
Gain error			±0.55				LSB	Ext. Ref.*
			±3				LSB	Int. Ref.*
TEMPERATURE COEFFICIENTS (T _{min} to T _{max})	-							
Unipolar offset			7 ty	o., 10 n	nax.		ppm/°C	Ext. Ref.
			7 tyj	o., 10 n	nax.		ppm/°C	Int. Ref.
Bipolar offset			7 ty	o., 10 n	nax.		ppm/°C	Ext. Ref.
				p., 10 r	nax		ppm/°C	Int. Ref.
Gain				10 typ.			ppm/°C	Ext. Ref.
				50 typ.			ppm/°C	Int. Ref.
	ZN502CJ						·	
Linearity error				±1.0		±1.0	LSB	
Diff. linearity error				±1.0		±1.0	LSB	Note 1
Unipolar offset			±0.55	±1.0		±1.0	LSB	Ext. Ref.
	}		±0.55	±1.0		±1.0	LSB	Int. Ref.
Bipolar offset			±0.55	±1.0		±1.0	LSB	Ext. Ref.
			±0.55	±1.0		±1.0	LSB LSB	Int. Ref. Ext. Ref.*
Gain error			±0.55				LSB	Int. Ref.*
	<u> </u>		±3			<u> </u>	LOB	iiit. Nei.

^{*}See note 4

ELECTRICAL CHARACTERISTICS (Cont.)

PLESSEY SEMICONDUCTORS

		T _{emb} = +25°C		Over Spec		T-51-10-10		
Parameter	Version	Min.	Тур.	Max.	Min.	Max.	Units	Conditions
TEMPERATURE COEFFICIENTS (T _{min} to T _{max}) Unipolar offset Bipolar offset Gain		15 typ., 20 max. 15 typ., 20 max. 15 typ., 20 max. 15 typ., 20 max. 20 typ. 50 typ.					ppm/°C ppm/°C ppm/°C ppm/°C ppm/°C ppm/°C	Ext. Ref. Int. Ref. Ext. Ref. Int. Ref. Ext. Ref.* Int. Ref.*
	ZN502E			meter v or ZN50				
Resolution Conversion time (min) DAC reference I _{ref} Nominal analogue input range Supply rejection Supply voltage +V _{CC} -V _{CC} Supply current +I _{CC} -I _{CC} Power consumption INTERNAL VOLTAGE REFERENCE Output voltage Output voltage	All types All types ZN501AJ	10 10 0.25 -2.5 - +4.5 -4.5 -	- 15 0.5 - 0.1 +5 -5 30 21 255	- 20 1.0 +2.5 - +5.5 -5.5 40 28 340	- +4.5 -4.5 - - -	- 20 1.0 - + 5.5 - 5.5 - -	bits µs mA V % per V V mA mA mW	Note 2 Note 5 Note 3 +V _{CC} = +5V -V _{CC} = -5V
tolerance V _{REF} temp. coeff. Slope impedance Max. load current	ZN502CJ ZN502E All types	- - - -	- - 0.75 ±2.0	±5.0 ±5.0 - -		- 50 -	% % ppm/°C Ω mA	
LOGIC START CONVERT SC High level inpV V _{ih} Low level inpV V _{il} High level inpI I _{ih} High level inpI I _{ih} Low level inpI I _{il}	All types	2.0 - - -	- 18.0 8.0 4.0	- 0.8 - - -	2.0 - - - -	- 0.8 - - -	V V μΑ μΑ	$V_{CC} = \pm 5.5V \\ V_{in} = 5.5V \\ V_{CC} \pm 5.5V \\ V_{in} = 2.4V \\ V_{CC} \pm 5.5V \\ V_{in} + 0.4V$

^{*}See note 4

LECTRICAL CHARACTERISTICS (Cont.)								
		T _{amb} = +25°C			Over Spec			
Parameter	Version	Min.	Тур.	Max.	Min.	Max.	Units	Conditions
LOGIC	All types							
BYTE 1 and 2							1	
High level inpV Vih		2.0	-	-	2.0	-	V	
Low level inpV Vil		_	-	0.8	-	0.8	V	
High level inpl lih		-	18.0	-	-	-	μΑ	$V_{CC} = \pm 5.5V$ $V_{in} = 5.5V$
High level inpl l _{ih}		- .	12.0	-	-	-	μΑ	$V_{CC} = \pm 5.5V$ $V_{in} = 2.4V$
Low level inpl l _{il}		-	2.0	-	-	-	μΑ	$V_{CC} = \pm 5.5V$ $V_{in} = 0.4V$
CLOCK	All types							
CLOCK high period		0.5	_	_	_	_	μs	
Max. clock frequency		550	730	1100	550	730	KHz	
High level inpV Vih		2.0	_		2.0	-	V	
Low level inpV Vil		-	-	0.8	_	0.8	V	
High level inpl lih		-	15.0	_	_	-	μΑ	$V_{CC} = \pm 5.5V$ $V_{in} = 5.5V$
High level inpl l _{ih}		-	5.0	_	-	-	μΑ	$V_{CC} = \pm 5.5V$ $V_{in} = 2.4V$
Low level inpl Ii		-	3.0	-	-	-	μΑ	$V_{CC} = \pm 5.5V$ $V_{in} = 0.4V$
High level OPV Voh	All types	2.4	-	-	2.4		V	$V_{CC} = \pm 5V$
Low level OPV Vol		– .	-	0.4	-	0.4	\ V	
High level OPI Ioh		-	-	- 700	_	_	μΑ	
Low level OPI IoI		-	-	2.0	-	-	mA	_
Three-state DISABLE output leakage			_	± 2.0	-	-	μΑ	V _{out} = 1.3V
BYTE input to data		_	200	260	-	-	ns	

Note 1 No missing codes over full temperature range at appropriate accuracy.

Note 2 The maximum conversion time is 20µs. This corresponds to a clock rate of 550KHz based on 11 clock periods per conversion cycle (see timing diagram). This provides an update rate of 50KHz.

220

80

120

60

180

260

100

140

100

ns

ns

ns

ns

ns

ns

Note 6

Note 3 Single polarity and other input ranges may be provided by different input resistor values.

100

60

100

30

100

Note 4 Gain error is trimmable to zero with the aid of R3.

Note 5 The full scale D-A output current $I_{out} = 4$ times I_{ref} . For optimum performance $I_{ref} = 0.5$ mA.

Note 6 Refer to Fig. 9.

output delays **ENABLE/DISABLE**

Delay time TE1

SC pulse width

SC input to STATUS

TEO

TD1

TDO

GENERAL CIRCUIT OPERATION

The ZN501 utilises the successive approximation technique. Upon receipt of a negative-going pulse at the SC input the STATUS output goes low, and the D-A converter input is set to the MSB. The resulting analogue output is compared with the unknown analogue input signal by means of the comparator. So if the analogue input is the larger, the MSB is left in circuit and if not the MSB is removed. On the second clock pulse this sequence is repeated for the next most significant bit and so on until all the 10-bits

have been compared. On the 11th negative clock edge STATUS goes high indicating that the conversion is complete.

During a conversion BYTE 1 and BYTE 2 will normally be held high to keep the 3-state buffers in their high impedance state. Data can be read out by taking either BYTE 1 or BYTE 2 low, thus enabling the three-state outputs. BYTE 1 controls the 8 MSB's and BYTE 2 controls the 2 LSB's. Readout is non-destructive.

CONVERSION TIMING

The ZN501 will accept a low-going START CONVERT pulse, which can be completely asynchronous with respect to the clock, and will produce valid data between 10.5 and 11.5 clock pulses later depending on the relative timing of the CLOCK and START CONVERT signals.

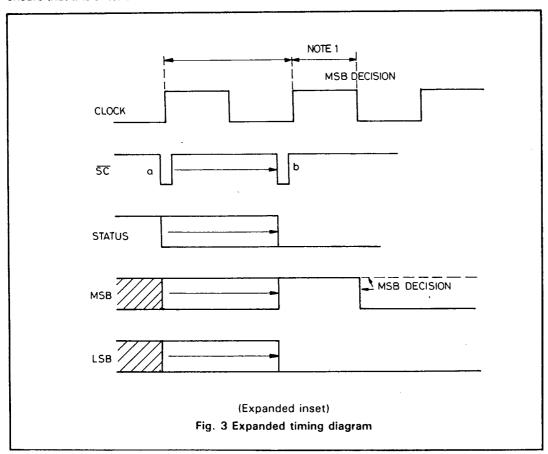
The converter is cleared by a low-going START CONVERT pulse, which sets the most significant bit and resets all the other bits and STATUS, Whilst the START CONVERT input is low the MSB output of the D-A converter is continuously compared with the analogue input, but otherwise the converter is inhibited. After the START CONVERT input goes high again the MSB decision is made and the successive approximation routine runs to completion.

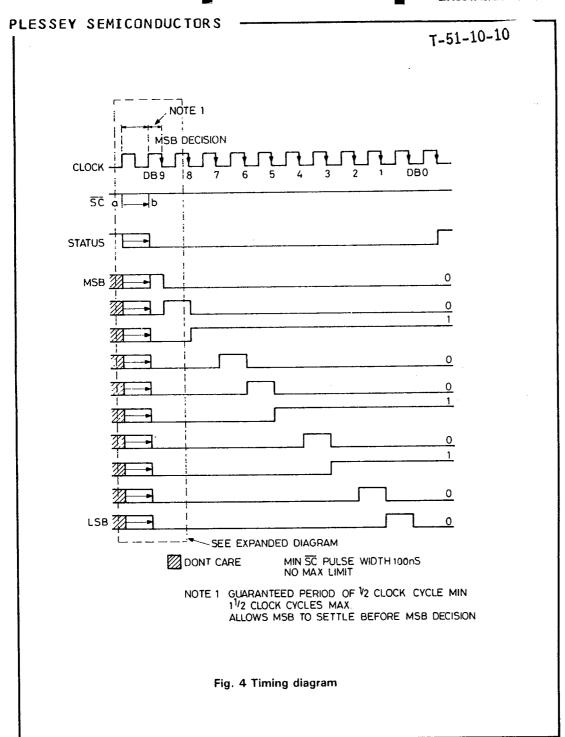
The SC pulse can be as short as 100ns; however the MSB must be allowed to settle for at least (625ns) before the MSB decision is made. To ensure that this criterion is met even with short

SC pulses the converter waits, after the SC input goes high, for a rising clock edge followed by a falling clock edge, the MSB decision being taken on the falling clock edge. This ensures that the MSB is allowed to settle for at least half a clock period, or (625ns) at maximum clock frequency. The clock high period and the SC pulse width must comply with this settling time i.e. clock high period + SC pulse width ≥625ns.

During a conversion the SC input is not locked out and if it is pulsed low at any time the conversion will restart.

At the end of a conversion STATUS waits 1 clock cycle before going high, so indicating that data is valid. The data outputs can be thus enabled anytime during a conversion and valid data will be available on the rising edge of the STATUS signal.





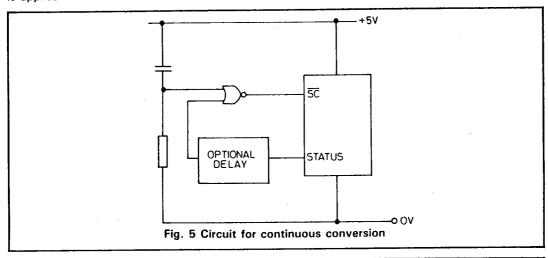
PLESSEY SEMICONDUCTORS

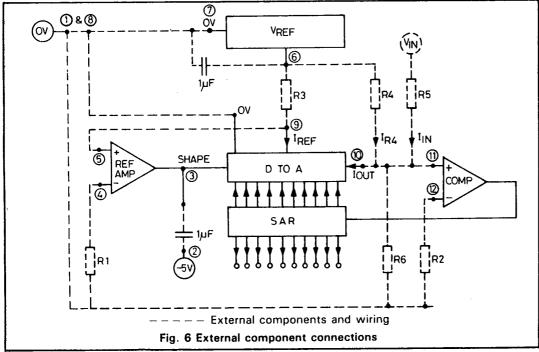
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CONTINUOUS CONVERSION

The converter can be made to cycle by inverting the STATUS output and feeding back to the SC input. To ensure that the converter starts reliably after power up an initial start pulse is required. This can be ensured by using a NOR gate instead of an inverter and feeding it with a positive going pulse which can be derived from a simple RC network that gives a single pulse when power is applied.

The propagation delay of the NOR gate determines the period over which STATUS remains high, during which time the data can be stored into latches. The time available for storing the data can be increased by inserting delays into the inverter path.





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CALCULATION OF EXTERNAL RESISTORS

If $V_{\text{in max}}$ is the voltage for the logic output to be all 1's.

 $V_{\text{in min}}$ is the voltage for the logic output to be all 0's.

$$I_{out} = I_{R4} + I_{in}$$

$$I_{out} = \frac{V_{ref}}{R4} + \frac{V_{in}}{R5}$$

$$\begin{split} \textbf{I}_{out} = \textbf{0} \text{ (When } \textbf{V}_{in} = \textbf{V}_{in \text{ min}} \textbf{)} \\ & \frac{\textbf{V}_{in \text{ min}}}{\textbf{R5}} = -\frac{\textbf{V}_{ref}}{\textbf{R4}} \\ \textbf{R4} = -\frac{\textbf{V}_{ref}}{\textbf{V}_{in \text{ min}}} \textbf{R5} \end{split}$$

$$\begin{split} I_{out}(f.s.) &= 2mA \colon \{When\ V_{in} = V_{in\ max}\} \\ &= \frac{V_{in\ max}}{R5} + \frac{V_{ref}}{R4} = I_{out}(f.s.) \\ &= \frac{V_{in\ min}}{R5} + \frac{V_{in\ max}}{R5} = I_{out}(f.s.) \end{split}$$

$$R5 = \frac{V_{in\ max} - V_{in\ min}}{I_{out}(f.s.)}$$

It is important for gain stability that $l_{out}(f.s.)$ of 2mA be kept constant, and this is done by the reference amplifier loop.

PLESSEY SEMICONDUCTORS

The current sources in the D-A itself cannot be checked directly so a number of reference current sources are distributed across the chip to monitor conditions all along the array.

So
$$I_{ref} = 0.5 \text{mA}$$

$$R3 = V_{ref}$$

$$0.5 \text{mA}$$

I_{out}(f.s.) is four times I_{ref}.

R3 can affect gain stability and thus requires to be of high quality. (Also slight variation in its value can act as a gain control).

R4 and R5 can affect offset stability and thus requires to be of high quality. (Also slight variations in the value of R4 can act as an offset control).

R1 and R2 supply the bias currents of the reference amplifier and comparator.

So
$$R1 = R3$$

and R2 = parallel combination of R4, R5 and R6

R6 should be chosen such that the parallel combination of R4, R5 and R6 is about $1.25 \mathrm{K}\Omega$ as this determines the D-A time constant and hence conversion time.

PLESSEY SEMICONDUCTORS

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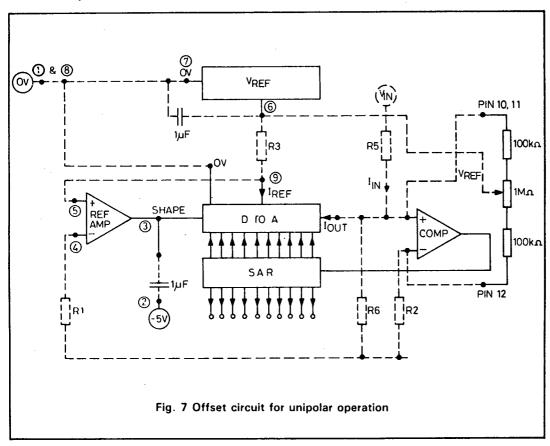
(THE FOLLOWING IS A TABLE OF VALUES TO GIVE EXAMPLES OF THE ABOVE EQUATIONS):

V _{in max}	V _{in min}	V _{ref}	R1 (1)	R2 (1)	R3	R4	R5	R6 (1)
+ 2.5	2.5	2.5	5K	1.25K	5K	2.5K	2.5K	∞
+ 2.5	2.5	5*	10K	1.25K	10K	5.0K	2.5K	5.0K
+ 2.5	o	2.5	5K	1.25K	5K	00	1.25K	∞
+ 5.0	0	2.5	5K	1.25K	5K	∞	2.5K	2.5K
+ 4.0	2.0	2.5	5K	1.25K	5K	3.75K	-3.0K	5.0K
+ 4.0	2.0	12*	24K	1.25K	24K	3.75K	3.0K	5.0K
÷ 10	10	2.5	5K	1.25K	5K	2.5K	10K	3.33K
+ 10	0	2.5	5K	1.25K	5K	∞	5K	1.66K

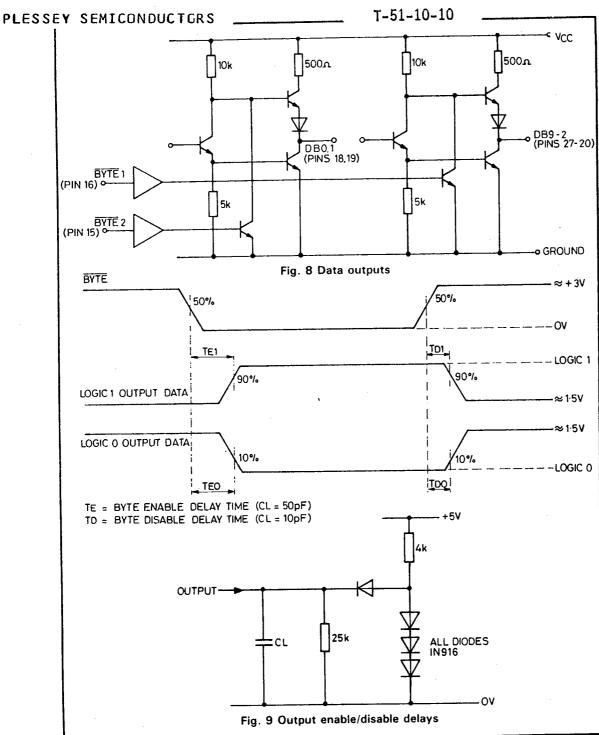
Note 1 Nearest prefered value may be used for R1, R2 and R6

For unipolar operation where R4 approaches (∞) and a zero adjustment is required, the following

offset circuit is suggested in place of R4.



^{*}Note 2 External reference.



PLESSEY SEMICONDUCTORS

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DATA OUTPUTS

The ZN501 has true three-state output buffers on chip, hence eliminating the need for external buffers and latch circuitry.

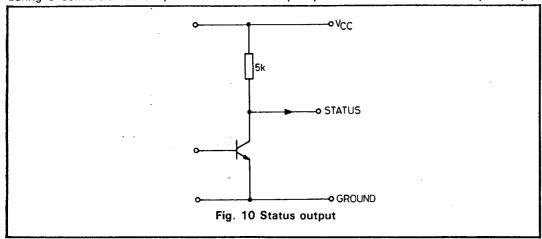
The two BYTE select pins BYTE 1 and BYTE 2, control outputs DB9 to DB2, and outputs DB1 to DB0 respectively.

BYTE 1 and BYTE 2 will normally be held high during a conversion to keep the three-state

buffers in their high impedance state, and when data is ready, which will be signalled by a high going STATUS pulse, it can easily be read out by taking BYTE 1 and BYTE 2 low.

(A test circuit and timing diagram for the output enable/disable delays are given).

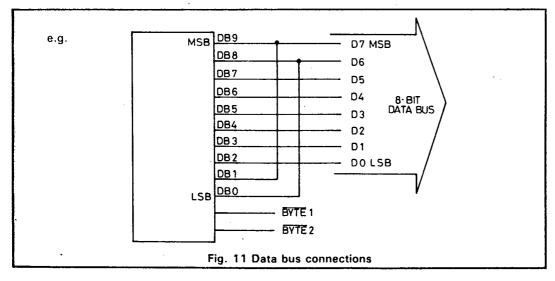
The STATUS output shown utilises a 5K internal pullup resistor for CMOS/TTL compatibility.



DATA BUS CONNECTIONS

The ZN501 can be connected directly to an 8-bit microprocessor bus, where the two LSB's would normally be hardwired to the desired upper bits, usually the 2 MSB's. Hence the data would be transferred in two words with control of them, from BYTE 1 and BYTE 2.

For use with a 16-bit microprocessor, BYTE 1 and BYTE 2 would be tied together and all 10 bits would be enabled simultaneously. The 10-bit word could then be placed at either the higher or lower end of the 16-bit bus.



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ZN501AJ/ZN502E/CJ

BY	TE	1

					PL	ESSEY	SEM:	ICONDUCTORS
DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	
D7	D6	D5	D4	D3	D2	D1	DO	

BYTE 2

DB1	DB0	Х	Х	Х	×	×	х

DATA TRANSFERRED IN TWO WORDS

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UNIPOLAR ADJUSTMENT PROCEDURE

(i) Apply continuous START CONVERT pulse at intervals long enough to allow a complete conversion and monitor the digital outputs.

OFFSET SETTING

(ii) Apply ½LSB to V_{in} and adjust the offset CIRCUIT until DBO (LSB) just flickers between 0 and 1 with all the other bits at 0. i.e. for transition 0000000000 to 0000000001.

GAIN SETTING

(iii) Apply full-scale minus 1.½LSB to $V_{\rm in}$ and adjust gain until DBO (LSB) just flickers between 0 and 1 with all other bits at 1. i.e. for transition 1111111111 to 111111110.

Note: R3 GAIN ADJUSTMENT.

UNIPOLAR SETTING-UP POINTS

Input range +FS	½LSB	F.S. – 1. ½ LSB
+ 2.5V	1.22mV	2.4963V
+ 5.0V	2.441mV	4.9926V

 $1LSB = \frac{FS}{1024}$

UNIPOLAR LOGIC CODING

Analogue input (Nominal code centre value)	Digital output code MSB LSB		
FS - 1LSB	111111111		
FS - 2LSB	111111110		
¾ .FS	110000000		
⅓.FS + LSB	100000001		
½ .FS	100000000		
⅓.FS - 1LSB	011111111		
1/4 .FS	010000000		
1LSB	000000001		
0	000000000		

ZN501AJ/ZN502E/CJ

PLESSEY SEMICONDUCTORS

BIPOLAR ADJUSTMENT PROCEDURE

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(i) Apply continuous START CONVERT pulses at intervals long enough to allow a complete conversion and monitor the digital outputs.

OFFSET SETTING

(ii) Apply - (FS - ½.LSB) to V_{in} and adjust offset control until DBO (LSB) output just flickers between 0 and 1 with all other bits at 0.

i.e. for transistions 0000000000 to 000000001.

Note: R4 OFFSET ADJUSTMENT.

GAIN SETTING

(iii) Apply + (FS - $1\frac{1}{2}$.LSB) to V_{in} and adjust gain until DBO (LSB) just flickers between 0 and 1 with all other bits at 0.

i.e. for transition 1111111111 to 111111110.

Note: R3 GAIN ADJUSTMENT.

BIPOLAR SETTING-UP POINTS

Input range ±FS	(FS – ½ .LSB)	+ (F.S 1.1/2.LSB)
± 2.5V	- 2.4976V	+ 2.4927V
± 5.0V	- 4.9951V	+ 4.9854V

 $1LSB = 2FS \over 1024$

BIPOLAR LOGIC CODING

Analogue input	Digital output code		
(Nominal code centre value)	MSB LSB		
+ (FS · 1LSB)	111111111		
+ (FS · 2LSB)	111111110		
+ (½ .FS)	110000000		
+ (1LSB)	100000001		
0 - (1LSB)	100000000		
- (1235) - (½.FS) - (FS - 1LSB)	010000000		
- FS	000000000		